

L Number	Hits	Search Text	DB	Time stamp
1	1	debye adj length near3 source near3 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:10
2	3	881254.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:12
3	0	body adj bias and vmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:17
4	1	body near2 bias\$3 and (vmos or vmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:18
5	39	(body near2 (bias\$3 or contact)) and (vmos or vmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:19
6	17	(body adj (bias\$3 or contact)) and (vmos or vmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:20
7	3	(body adj (bias\$3 or contact)) and (vmos or vmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:33
8	0	(body adj (bias\$3 or contact)) near10 (vmos or vmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 09:22
9	3	(body adj (bias\$3 or contact) or source-body adj contact) and (vmos or vmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 10:45
10	7	source near2 body near2 contact same threshold adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 10:47
11	4	(source near2 body near2 contact same threshold adj voltage) not soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 12:33
12	2594	((257/327) or (257/328) or (257/329) or (257/330) or (257/331) or (257/332) or (257/333) or (257/335)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 12:33
13	17	((257/327) or (257/328) or (257/329) or (257/330) or (257/331) or (257/332) or (257/333) or (257/335)).CCLS.) and body near3 contact and (vmos or vmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 12:34
-	5	("4961100") or ("5430315") or ("5877538") or ("5998834") or ("6096608")).PN.	USPAT	2002/09/23 09:32

-	3	((("4961100") or ("5430315") or ("5877538") or ("5998834") or ("6096608"))).PN.) and trench adj mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 09:15
-	1	trench adj mosfet.ti,ab. and 257/\$6.ccls. and doping adj profile	USPAT	2002/02/13 09:22
-	12	trench adj mosfet.ti,ab. and 257/\$6.ccls.	USPAT	2002/02/13 11:52
-	114	(trench and mosfet).ti,ab. and 257/\$6.ccls.	USPAT	2002/02/13 13:11
-	340	(257/302).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:21
-	354	(257/327).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	456	(257/328).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	356	(257/329).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	280	(257/331).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	239	(257/332).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	145	(257/333).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:26
-	503	(257/335).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:46
-	570	(257/330).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 13:27
-	477	((("257/335").CCLS.) not ("257/330").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 17:26
-	195	((("257/331").CCLS.) not ("257/330").CCLS.) not ("257/335").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 19:09
-	118	((("257/332").CCLS.) not ("257/330").CCLS.) not ("257/335").CCLS.) not ("257/331").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 19:21

-	70	(((((("257/333").CCLS.) not (("257/330").CCLS.)) not (("257/335").CCLS.)) not (("257/331").CCLS.)) not (("257/332").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 19:22
-	11	((p-well or channel adj region) near12 doping) near12 (graded or grading or profile)	EPO; JPO; IBM_TDB	2002/02/13 19:35
-	352	((("5430315") or ("4961100") or ("6096608") or ("5998834") or ("5877538") or ("6084264") or ("5917216") or ("5895952") or ("5693569") or ("5674766") or ("5661322") or ("5614751") or ("5610422") or ("5569949") or ("5349224") or ("5321289") or ("5298442") or ("5134448") or ("6274905") or ("6259134") or ("6198127") or ("6194273") or ("6188105") or ("6188104") or ("6163052") or ("6150693") or ("6147377") or ("6124608") or ("5821583") or ("6262470") or ("6262453") or ("6246090") or ("6242775") or ("6239465") or ("6239464") or ("6225659") or ("6222230") or ("6194741") or ("6172398") or ("6168996") or ("6137136") or ("6060731") or ("6057558") or ("6043543") or ("6040600") or ("6040599") or ("6037628") or ("6020600") or ("5986304") or ("5969378") or ("5945708") or ("5929481") or ("5915180") or ("5914503") or ("5910669") or ("5831288") or ("5770878") or ("5751024") or ("5744826") or ("5689128") or ("6180958") or ("6114727") or ("6051488") or ("6051468") or ("5929482") or ("5895951") or ("5719409") or ("5714781") or ("5670803") or ("5637898") or ("5629543") or ("5623152") or ("5614749") or ("5410170") or ("5396093") or ("5385853") or ("5378914") or ("5365097") or ("5341011") or ("5078498") or ("5072266") or ("5021846") or ("5016068") or ("5016067") or ("5001526") or ("4992838") or ("4929987") or ("4503449") or ("4398339") or ("4329705") or ("4326332") or ("4303841") or ("4296429") or ("4219835") or ("4156289") or ("4116720") or ("4105475") or ("4048649") or ("4003126") or ("6312993") or ("6194761") or ("6144067") or ("5856692") or ("5558313") or ("5489787") or ("5442214") or ("5012306") or ("6285060") or ("6284604") or ("6262439") or ("6201280") or ("6133587") or ("6118150") or ("6060747") or ("6060746") or ("6049108") or ("6002143") or ("5998837") or ("5998836") or ("5894149") or ("5883411") or ("5877528") or ("5844273") or ("5828100") or ("5742076") or ("5627393") or ("6218217") or ("6204533") or ("6180966") or ("6005271") or ("5801417") or ("5592005") or ("5576567") or ("5493134") or ("4954854") or ("3761785") or ("5298781") or ("4914058") or ("4830978") or ("4250519") or ("4222063"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 19:53

0 ("JP-6053514") or ("JP-6021468") or  
 ("JP-6021461") or ("JP-6005857") or  
 ("JP-6005853") or ("JP-5335581") or  
 ("JP-5226661") or ("JP-5082792") or  
 ("JP-5048090") or ("JP-4360572") or  
 ("JP-4290271") or ("EP-580452") or  
 ("EP-562257") or ("EP-345380") or  
 ("EP-299505") or ("EP-164095") or  
 ("EP-159663") or ("EP-91686") or  
 ("JP-5090400") or ("EP-869552") or  
 ("JP-2001164")).PN.

USPAT; 2002/02/13 19:58  
 US-PGPUB;  
 EPO; JPO;  
 DERWENT;  
 IBM\_TDB

62 JP-06053514\$-\$.did.  
 JP-06021468\$-\$.did.  
 JP-06021461\$-\$.did.  
 JP-06005857\$-\$.did.  
 JP-06005853\$-\$.did.  
 JP-05335581\$-\$.did.  
 JP-05226661\$-\$.did.  
 JP-05082792\$-\$.did.  
 JP-05048090\$-\$.did.  
 JP-04360572\$-\$.did.  
 JP-04290271\$-\$.did.  
 EP-580452\$-\$.did.  
 EP-562257\$-\$.did.  
 EP-345380\$-\$.did.  
 EP-299505\$-\$.did.  
 EP-164095\$-\$.did.  
 EP-159663\$-\$.did.  
 EP-91686\$-\$.did.  
 JP-05090400\$-\$.did.  
 EP-869552\$-\$.did.  
 JP-02001164\$-\$.did.

USPAT; 2002/02/13 20:00  
 US-PGPUB;  
 EPO; JPO;  
 DERWENT;  
 IBM\_TDB





-	3	4250519.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 10:21
-	39	((gold or platinum) near12 recombination adj center) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 10:41
-	3	((gold or platinum) near12 recombination adj center) and (vmost or vertical adj mosfet or trench mosfet) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 11:45
-	41	257/\$6.ccls. and (oxynitride near12 gate adj insulat\$3 adj (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 12:00
-	5	(257/\$6.ccls. and (oxynitride near12 gate adj insulat\$3 adj (film or layer))) and mosfet.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 11:47
-	25	257/\$6.ccls. and (silicon adj oxynitride near12 gate adj insulat\$3 adj (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 12:01
-	2	257/\$6.ccls. and (silicon adj oxynitride near12 gate adj insulat\$3 adj (film or layer)) and (vertical adj mosfet or trench adj mosfet or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 12:03
-	4	257/\$6.ccls. and (silicon adj oxynitride near12 gate adj insulat\$3 adj (film or layer)) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 12:04
-	1	257/\$6.ccls. and (silicon adj oxynitride near12 gate adj insulat\$3 adj (film or layer)) and (advantage\$6 near12 oxynitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 12:29
-	47	fixed adj charge near12 insulat\$3 adj (layer or film) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 13:30
-	3	4250519.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 13:30
-	5	4116720.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 13:40
-	0	44250519.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 13:40
-	3	4250519.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 13:40

-	3	5025293.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:04
-	1	down-conversion near6 terahertz	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:05
-	2337	((257/327) or (257/328) or (257/329) or (257/330) or (257/331) or (257/332) or (257/333) or (257/335)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 10:58
-	69	((257/327) or (257/328) or (257/329) or (257/330) or (257/331) or (257/332) or (257/333) or (257/335)).CCLS.) and (vmos or v-mos or vertical near3 mos\$3) and profile near12 (dopant or doping or concentration near3 impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:00
-	2	trench adj gate.ti,ab,clm. and lateral adj MOS.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 18:28
-	44	trench adj gate.ti,ab,clm. and polysilicon adj gate.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 18:28
-	12	"4250519"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 09:32
-	52	"4116720"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 09:32